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Diodes Incorporated DMN10H120SE-13

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Datasheet of DMN10H120SE-13 - MOSFET N-CH 100V 3.6A SOT223

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**DMN10H120SE** 

#### 100V N-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C		
400)/	$110m\Omega$ @ $V_{GS}$ = $10V$	3.6A		
100V	122mΩ @ $V_{GS}$ = 6.0 $V$	3.4A		

## **Description**

This new generation MOSFET is designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

## **Applications**

- DC-DC Converters
- Power Management Functions

### **Features and Benefits**

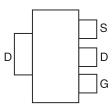
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

### **Mechanical Data**

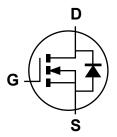
- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound;
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
   Solderable per MIL-STD-202, Method 208 <a> § 3</a>
- Weight: 0.112 grams (Approximate)







Pin Out - Top View



**Equivalent Circuit** 

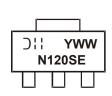
## Ordering Information (Note 4)

Part Number	Qualification	Case	Packaging
DMN10H120SE-13	Standard	SOT223	2,500/Tape & Reel

#### Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



SOT223

O!! = Manufacturer's Marking N120SE = Marking Code YWW = Date Code Marking Y or Y = Year (ex: 5 = 2015) WW = Week (01 - 53)

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**DMN10H120SE** 

### Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage			$V_{DSS}$	100	V
Gate-Source Voltage			$V_{GSS}$	±20	V
Continuous Drain Current (Note 6) $V_{GS} = 10V$ Steady $T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$		I <sub>D</sub>	3.6 2.9	А	
Pulsed Drain Current (10µs pulse, duty cycle ≦1%)			I <sub>DM</sub>	16	Α
Maximum Body Diode Continuous Current (Note 6)			Is	2.5	А

## Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Units	
Total Power Dissipation	(Note 5)	D-	1.3	W
Total Power Dissipation	(Note 6)	P <sub>D</sub>	2.1	
Thermal Begintance, Junction to Ambient	(Note 5)	$R_{ hetaJA}$	94	°C/W
Thermal Resistance, Junction to Ambient	(Note 6)		58	
Thermal Resistance, Junction to Case (Note 6)		R <sub>θ</sub> JC	8.2	
Operating and Storage Temperature Range		T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	°C

## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	100	_	_	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1.0	μA	V <sub>DS</sub> = 80V, V <sub>GS</sub> = 0V	
Gate-Body Leakage	I <sub>GSS</sub>	_	_	±100	nA	V <sub>GS</sub> = ±20V, V <sub>DS</sub> = 0V	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(th)</sub>	1.5	2.6	3.0	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	0	_	77	110	mΩ	$V_{GS} = 10V, I_D = 3.3A$	
Static Drain-Source On-Resistance	R <sub>DS (ON)</sub>	_	84	122	11122	V <sub>GS</sub> = 6.0V, I <sub>D</sub> = 3.0A	
Diode Forward Voltage	$V_{SD}$	_	8.0	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 3.2A	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C <sub>iss</sub>		549	_		V <sub>DS</sub> = 50V, V <sub>GS</sub> = 0V, f = 1.0MHz	
Output Capacitance	Coss	_	41	_	pF		
Reverse Transfer Capacitance	C <sub>rss</sub>	_	19	_			
Gate Resistance	$R_g$	_	1.6	_	Ω	VDS = 0V, VGS = 0V, f = 1.0MHz	
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	10	_		V <sub>DS</sub> = 50V, I <sub>D</sub> = 3.3A	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	_	5.2		nC		
Gate-Source Charge	Q <sub>gs</sub>	_	2.3	_	IIC		
Gate-Drain Charge	Q <sub>gd</sub>	_	2.6	_			
Turn-On Delay Time	t <sub>D(on)</sub>	_	3.8	_		$V_{DD} = 50V, V_{GS} = 10V,$ $R_G = 6.0\Omega, I_D = 3.3A$	
Turn-On Rise Time	t <sub>r</sub>	_	1.8	_	. 0		
Turn-Off Delay Time	t <sub>D(off)</sub>	_	11	_	nS		
Turn-Off Fall Time	t <sub>f</sub>	_	2.5	_			
Reverse Recovery Time	t <sub>rr</sub>	_	21	_	nS	V <sub>GS</sub> = 0V, I <sub>S</sub> =1.1A, di/dt=100A/μs	
Reverse Recovery Charge	Qrr	_	17	_	nC	VGS - υν, IS-1.1A, αι/αι-100A/μS	

5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

7. Short duration pulse test used to minimize self-heating effect. 8. Guaranteed by design. Not subject to product testing.

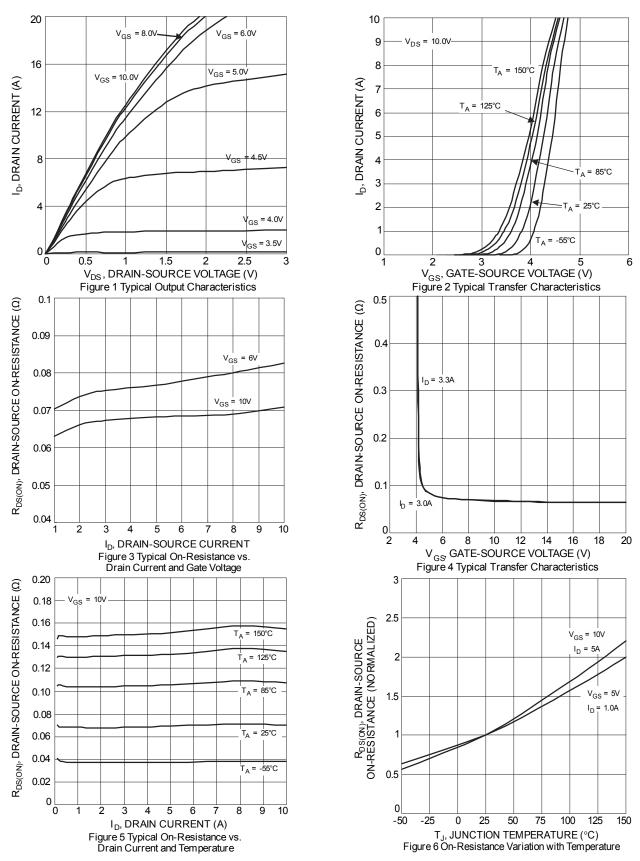
<sup>6.</sup> Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate

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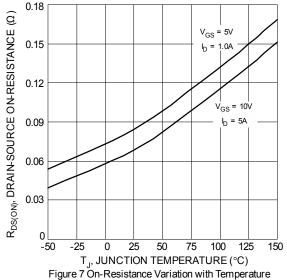
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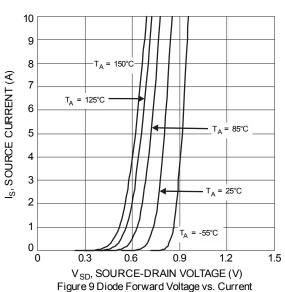


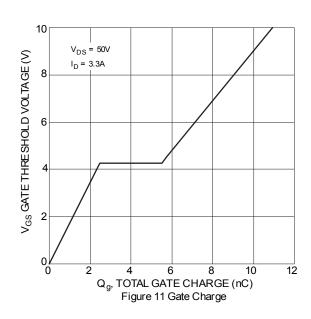
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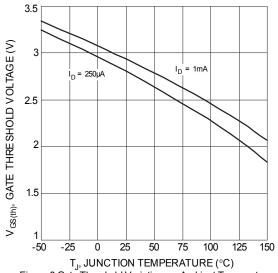
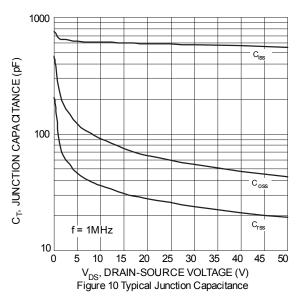
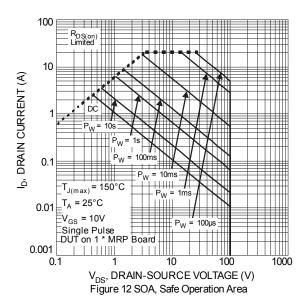


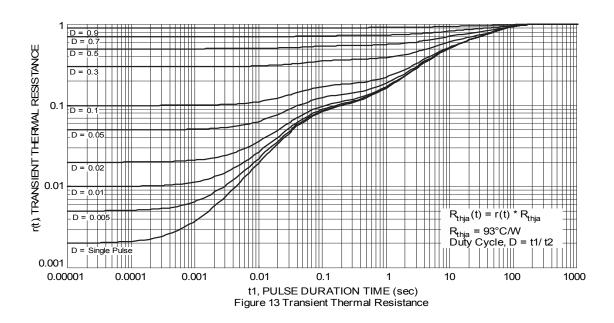
Figure 8 Gate Threshold Variation vs. Ambient Temperature





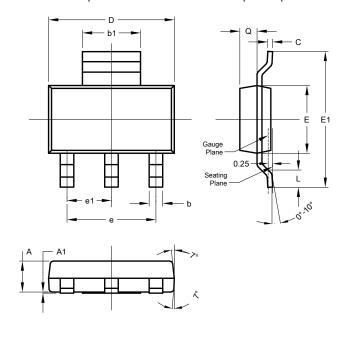






## Package Outline Dimensions & Suggested Pad Layout

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223						
Dim	Min	Max	Тур			
Α	1.55	1.65	1.60			
A1	0.010	0.15	0.05			
b	0.60	0.80	0.70			
b1	2.90	3.10	3.00			
C	0.20	0.30	0.25			
D	6.45	6.55	6.50			
Е	3.45	3.55	3.50			
E1	6.90	7.10	7.00			
е	-	-	4.60			
e1	-	ı	2.30			
L	0.85	1.05	0.95			
Q	0.84	0.94	0.89			
All Dimensions in mm						



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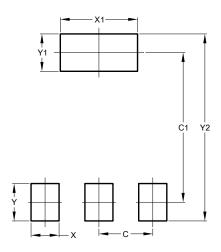
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DMN10H120SE

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)				
С	2.30				
C1	6.40				
Х	1.20				
X1	3.30				
Υ	1.60				
Y1	1.60				
C2	8.00				

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